

KSC5021F

High Voltage and High Reliability

- High Speed Switching : $t_F = 0.1 \mu s(Typ.)$
- Wide SOA



NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	5	Α
I _{CP}	Collector Current (Pulse)	10	Α
I _B	Base Current	2	Α
P _C	Collector Dissipation (T _C =25°C)	40	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics ${\rm T_{C}\text{=}25^{\circ}C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800			V
BV _{CEO}	Collector-Emitter Sustaining Voltage	$I_{C} = 5mA, I_{B} = 0$	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 2.5A$, $I_{B1} = -I_{B2} = 1A$ L = 1mH, Clamped	500			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$ $V_{CE} = 5V, I_{C} = 3A$	15 8		50	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1.5	V
C _{ob}	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		80		pF
f _T	Current Gain Bandwidth Product	V _{CE} = 10V, I _C = 0.6A		15		MHz
t _{ON}	Turn ON Time	V _{CC} = 200V			0.5	μs
t _{STG}	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$			3	μs
t _F	Fall Time	$R_L = 50\Omega$			0.3	μs

h_{FE} Classification

Classification	R	0	
Classification	45.00	20 40	00 50
n _{FE1}	15 ~ 30	20 ~ 40	30 ~ 50

Typical Characteristics

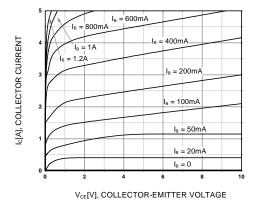


Figure 1. Static Characteristic

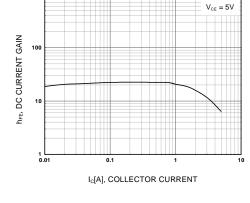


Figure 2. DC current Gain

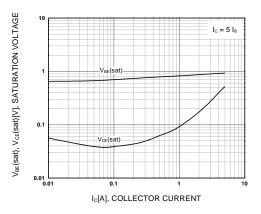


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

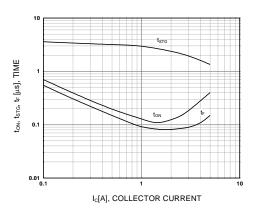


Figure 4. Switching Time

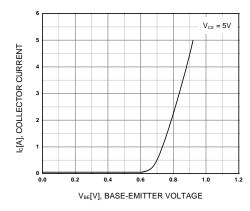


Figure 5. Base-Emitter On Voltage

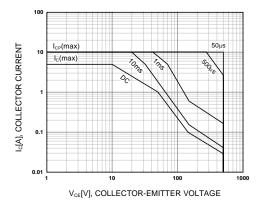


Figure 6. Safe Operating Area

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Typical Characteristics (Continued)

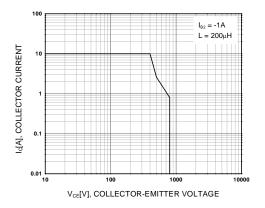


Figure 7. Reverse Bias Safe Operating Area

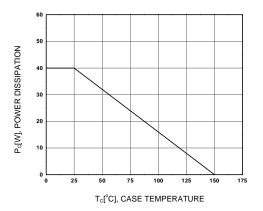
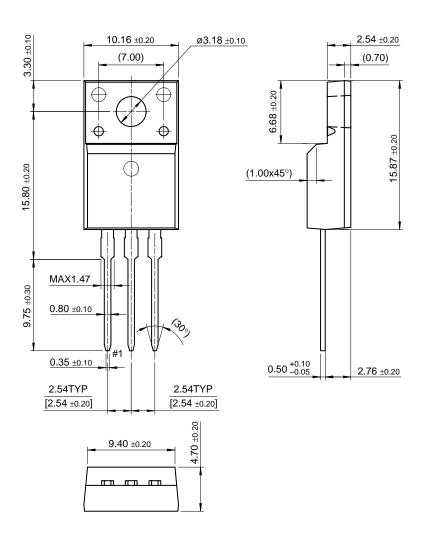


Figure 8. Power Derating

Package Demensions

TO-220F



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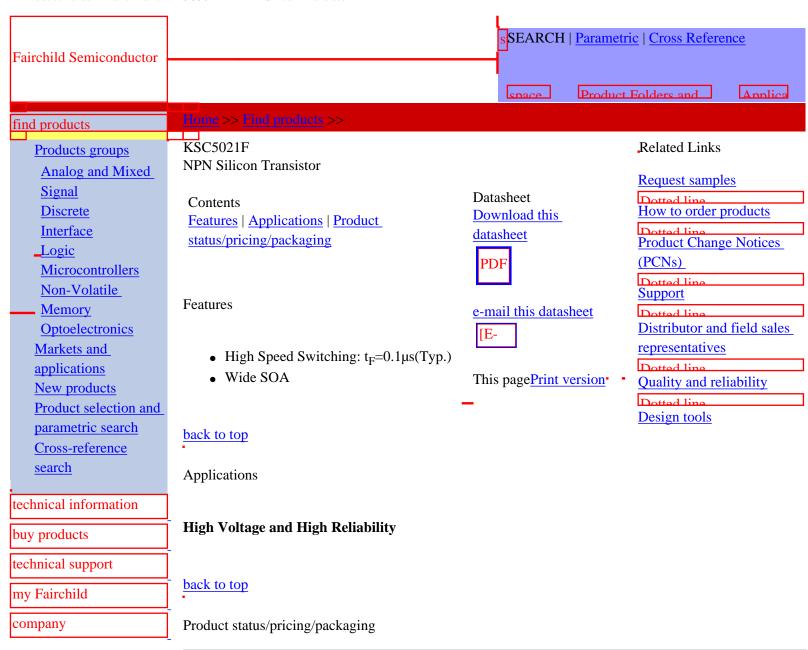
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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Product	Product status	Pricing*	Package type	Leads	Packing method
KSC5021FO	Full Production	\$0.61	<u>TO-220F</u>	3	BULK
KSC5021FOTU	Full Production	\$0.61	<u>TO-220F</u>	3	RAIL
KSC5021FYTU	Full Production	\$0.61	<u>TO-220F</u>	3	RAIL
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